

## ABSTRACT OF THE DISCLOSURE

An object of the invention to provide a semiconductor laser device fabrication method that can suppress inadvertent crosstalk while maintaining high relative position accuracy for a plurality of laser elements. In order to achieve this object, a plurality of emission sections are first formed on a single substrate, and the substrate is mounted on a sub mount. Then, the substrate on the sub mount is cut at a midway point between the emission sections. A laser device so fabricated includes two laser elements that are monolithically formed, thereby providing the laser elements with high relative position accuracy. Further, the substrate is cut between the laser elements, thereby preventing transfer of heat or electricity through the substrate. As a result, inadvertent thermal and electrical crosstalk can be effectively suppressed.